

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at <u>www.onsemi.com</u>

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor dates sheds, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor dates sheds and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use on similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor and its officers, employees, subsidiaries, affliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out or i, directly or indirectly, any lay bed ON Semiconductor and its officers, employees, ween if such claim alleges that ON Semiconductor was negligent regarding the d

October 1987 Revised April 2002

CD4093BC Quad 2-Input NAND Schmitt Trigger

General Description

The CD4093B consists of four Schmitt-trigger circuits. Each circuit functions as a 2-input NAND gate with Schmitt-trigger action on both inputs. The gate switches at different points for positive and negative-going signals. The difference between the positive $\left(V_{T}^{+}\right)$ and the negative voltage

 (V_{T}^{-}) is defined as hysteresis voltage (V_{H}).

All outputs have equal source and sink currents and conform to standard B-series output drive (see Static Electrical Characteristics).

Features

- Wide supply voltage range: 3.0V to 15V
- Schmitt-trigger on each input
- with no external components
- Noise immunity greater than 50%
- Equal source and sink currents
- No limit on input rise and fall time
- Standard B-series output drive
- Hysteresis voltage (any input) T_A = 25°C

Typical $V_{DD} = 5.0V V_H = 1.5V$ $V_{DD} = 10V V_H = 2.2V$ $V_{DD} = 15V V_H = 2.7V$

Guaranteed $V_{H} = 0.1 V_{DD}$

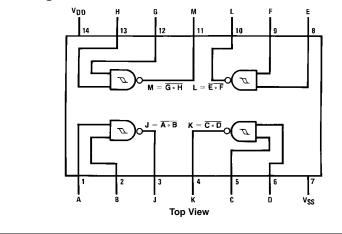
Applications

- Wave and pulse shapers
- · High-noise-environment systems
- Monostable multivibrators
- Astable multivibrators
- NAND logic

Ordering Code:

Order Number	Package Number	Package Description
CD4093BCM	M14A	14-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-012, 0.150" Narrow
CD4093BCN	N14A	14-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300" Wide
Devices also available	in Tape and Reel. Specify	by appending the suffix letter "X" to the ordering code.

Connection Diagram



CD4093BC

Absolute Maximum Ratings(Note 1) (Note 2)

DC Supply Voltage (V _{DD})	-0.5 to $+18$ V _{DC}
Input Voltage (V _{IN})	–0.5 to V_{DD} +0.5 V_{DC}
Storage Temperature Range (T_S)	$-65^{\circ}C$ to $+150^{\circ}C$
Power Dissipation (P _D)	
Dual-In-Line	700 mW
Small Outline	500 mW
Lead Temperature (TL)	
(Soldering, 10 seconds)	260°C

Recommended Operating Conditions (Note 2)

DC Supply Voltage (V_{DD}) Input Voltage (V_{IN}) 3 to 15 V_{DC} 0 to V_{DD} V_{DC}

conditions for actual device operation. Note 2: $V_{SS} = 0V$ unless otherwise specified.

DC Electrical Characteristics (Note 2)

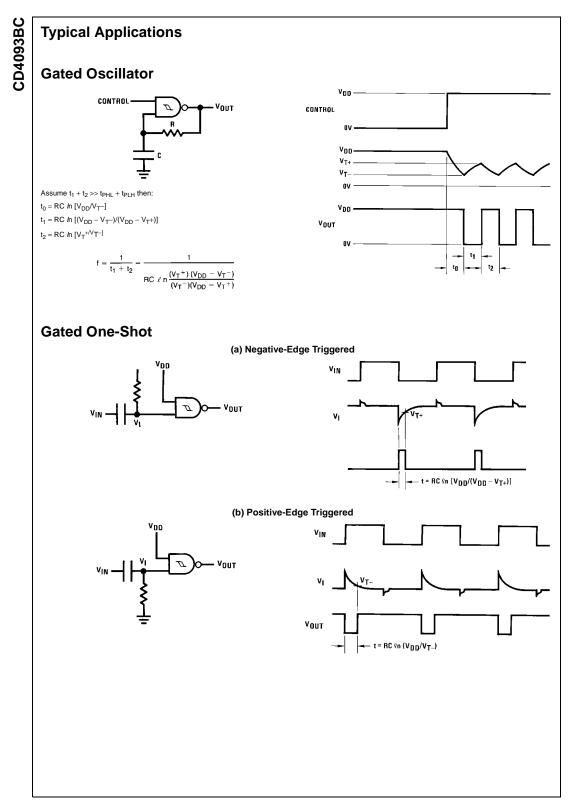
Cumber!	Devementer	0	-55	–55°C		+25°C			+125°C	
Symbol	Parameter	Conditions	Min	Max	Min	Тур	Max	Min	Max	Units
I _{DD}	Quiescent Device	$V_{DD} = 5V$		0.25			0.25		7.5	
	Current	$V_{DD} = 10V$		0.5			0.5		15.0	μA
		$V_{DD} = 15V$		1.0			1.0		30.0	
V _{OL}	LOW Level	$V_{IN} = V_{DD,} I_O < 1 \ \mu A$								
0	Output Voltage	$V_{DD} = 5V$		0.05		0	0.05		0.05	
		$V_{DD} = 10V$		0.05		0	0.05		0.05	V
		$V_{DD} = 15V$		0.05		0	0.05		0.05	
V _{OH}	HIGH Level	$V_{IN} = V_{SS}, I_O < 1 \ \mu A$								
	Output Voltage	$V_{DD} = 5V$	4.95		4.95	5		4.95		
		$V_{DD} = 10V$	9.95		9.95	10		9.95		V
		$V_{DD} = 15V$	14.95		14.95	15		14.95		
	Negative-Going Threshold	I _O < 1 μA								
	Voltage (Any Input)	$V_{DD} = 5V, V_{O} = 4.5V$	1.3	2.25	1.5	1.8	2.25	1.5	2.3	
		$V_{DD} = 10V, V_{O} = 9V$	2.85	4.5	3.0	4.1	4.5	3.0	4.65	V
		$V_{DD} = 15V, V_{O} = 13.5V$	4.35	6.75	4.5	6.3	6.75	4.5	6.9	
V _T +	Positive-Going Threshold	I _O < 1 μA								
	Voltage (Any Input)	$V_{DD} = 5V, V_{O} = 0.5V$	2.75	3.6	2.75	3.3	3.5	2.65	3.5	
		$V_{DD} = 10V, V_{O} = 1V$	5.5	7.15	5.5	6.2	7.0	5.35	7.0	V
		$V_{DD} = 15V, V_O = 1.5V$	8.25	10.65	8.25	9.0	10.5	8.1	10.5	
V _H	Hysteresis (V _T + - V _T -)	$V_{DD} = 5V$	0.5	2.35	0.5	1.5	2.0	0.35	2.0	
	(Any Input)	$V_{DD} = 10V$	1.0	4.3	1.0	2.2	4.0	0.70	4.0	V
		$V_{DD} = 15V$	1.5	6.3	1.5	2.7	6.0	1.20	6.0	
I _{OL}	LOW Level Output	$V_{IN} = V_{DD}$								
	Current (Note 3)	$V_{DD} = 5V, V_{O} = 0.4V$	0.64		0.51	0.88		0.36		
		$V_{DD} = 10V, V_{O} = 0.5V$	1.6		1.3	2.25		0.9		mA
		$V_{DD} = 15V, V_{O} = 1.5V$	4.2		3.4	8.8		2.4		
I _{OH}	HIGH Level Output	$V_{IN} = V_{SS}$								
	Current (Note 3)	$V_{DD} = 5V$, $V_O = 4.6V$	-0.64		0.51	-0.88		-0.36		
		$V_{DD} = 10V, V_{O} = 9.5V$	-1.6		-1.3	-2.25		-0.9		mA
		$V_{DD} = 15V, V_{O} = 13.5V$	-4.2		-3.4	-8.8		-2.4		
I _{IN}	Input Current	$V_{DD} = 15V, V_{IN} = 0V$		-0.1	1	-10 ⁻⁵	-0.1	1	-1.0	
		V _{DD} = 15V, V _{IN} = 15V		0.1		10 ⁻⁵	0.1		1.0	μA

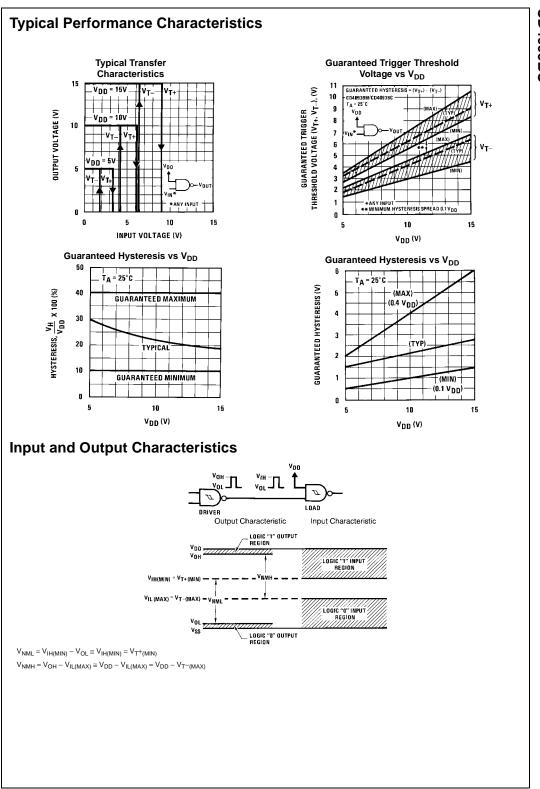
Note 3: I_{OH} and I_{OL} are tested one output at a time.

$T_A = 25^{\circ}C$, $C_L = 50 \text{ pF}$, $R_L = 200 \text{k}$, Input t_r , $t_f = 20 \text{ ns}$, unless otherwise specified							
Symbol	Parameter	Conditions	Min	Тур	Max	Units	
t _{PHL} , t _{PLH}	Propagation Delay Time	$V_{DD} = 5V$		300	450		
		$V_{DD} = 5V$ $V_{DD} = 10V$ $V_{DD} = 15V$		120	210	ns	
		$V_{DD} = 15V$		80	160		
t_{THL},t_{TLH}	Transition Time	$V_{DD} = 5V$		90	145		
		$V_{DD} = 10V$ $V_{DD} = 15V$		50	75	ns	
		$V_{DD} = 15V$		40	60		
C _{IN}	Input Capacitance	(Any Input)		5.0	7.5	pF	
CPD	Power Dissipation Capacitance	(Per Gate)		24		pF	

Note 4: AC Parameters are guaranteed by DC correlated testing.

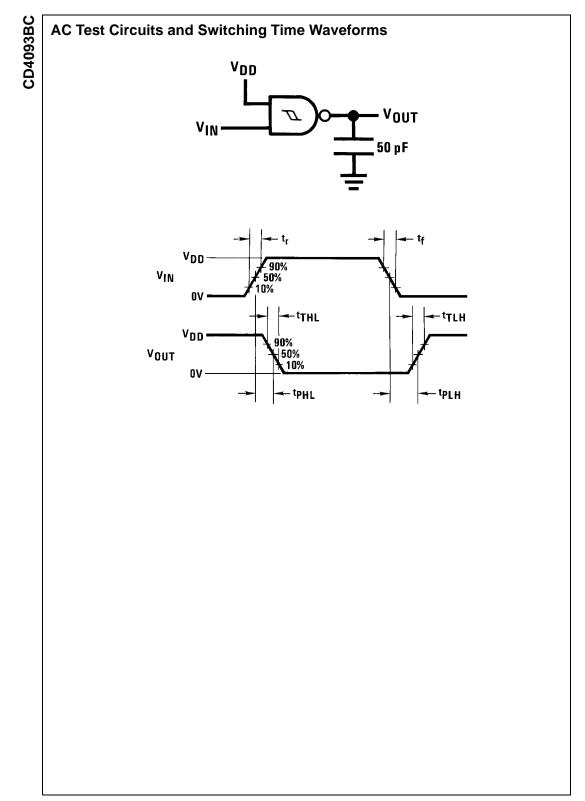
CD4093BC

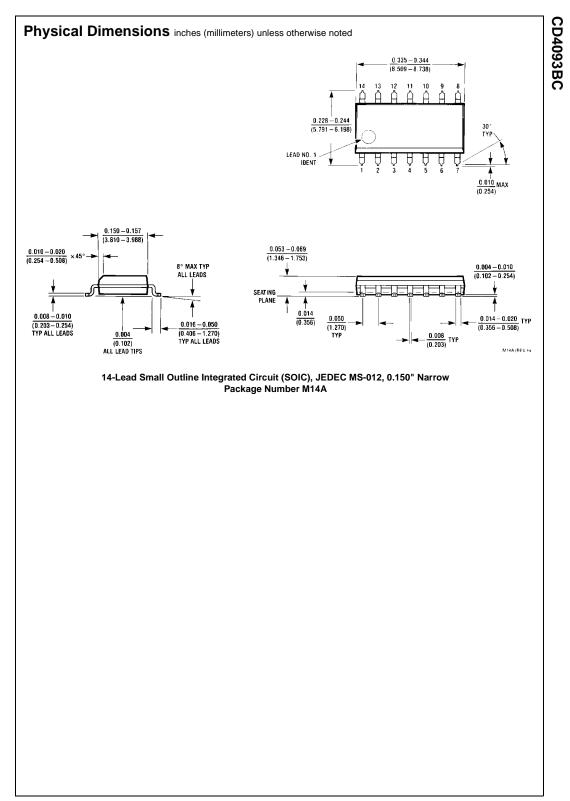


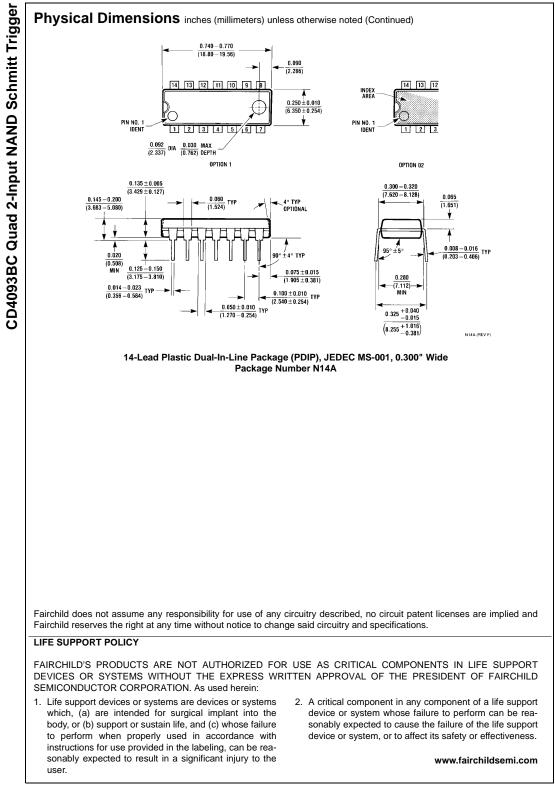


CD4093BC

www.fairchildsemi.com







www.fairchildsemi.com